

Description

The SX10N06S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 60V$ $I_D = 10A$

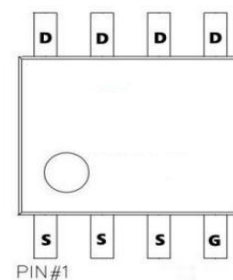
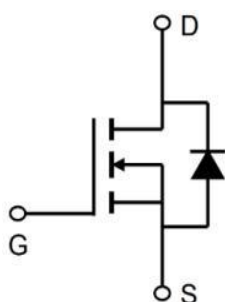
$R_{DS(ON)} < 40m\Omega$ @ $V_{GS} = 10V$

Application

LED lamp

Load switch

Uninterruptible power supply



Absolute Maximum Ratings@ $T_J = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	10	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.8	A
I_{DM}	Pulsed Drain Current	20	A
E_{AS}	Single Pulsed Avalanche Energy	25.5	mJ
$P_D @ T_C = 25^\circ C$	Power Dissipation	1.5	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	36	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60	65	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA	---	0.044	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =15A	---	28	40	mΩ
		V _{GS} =4.5V , I _D =7A	---	38	45	mΩ
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.6	2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	-4.8	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =48V , V _{GS} =0V , T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =15A	---	25.3	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2.5	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =48V , V _{GS} =10V , I _D =15A	---	19	---	nC
Q _{gs}	Gate-Source Charge		---	2.5	---	
Q _{gd}	Gate-Drain Charge		---	5	---	
Td(on)	Turn-On Delay Time	V _{DD} =30V , V _{GS} =10V , R _G =3.3Ω , I _D =15A	---	2.8	---	ns
T _r	Rise Time		---	16.6	---	
Td(off)	Turn-Off Delay Time		---	21.2	---	
T _f	Fall Time		---	5.6	---	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	1027	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	46	---	
I _s	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current	---	---	20	A
ISM	Pulsed Source Current ^{2,6}		---	---	40	A
VSD	Diode Forward Voltage ²	V _{GS} =0V , I _s =1A , T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	IF=15A , dI/dt=100A/μs , T _J =25°C	---	12.2	---	nS
Q _{rr}	Reverse Recovery Charge		---	7.3	---	nC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The power dissipation is limited by 175°C junction temperature
- 4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

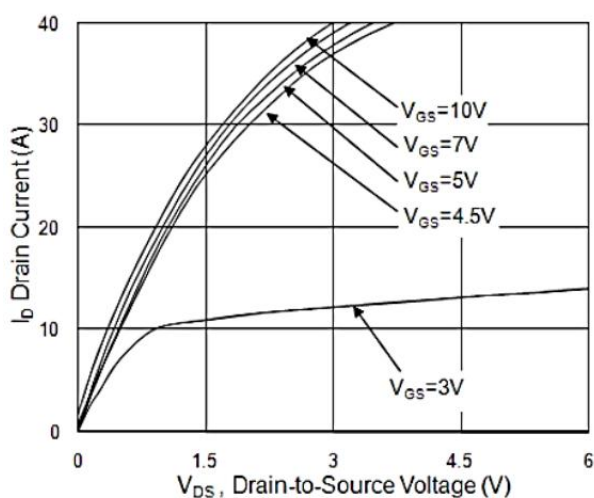


Fig.1 Typical Output Characteristics

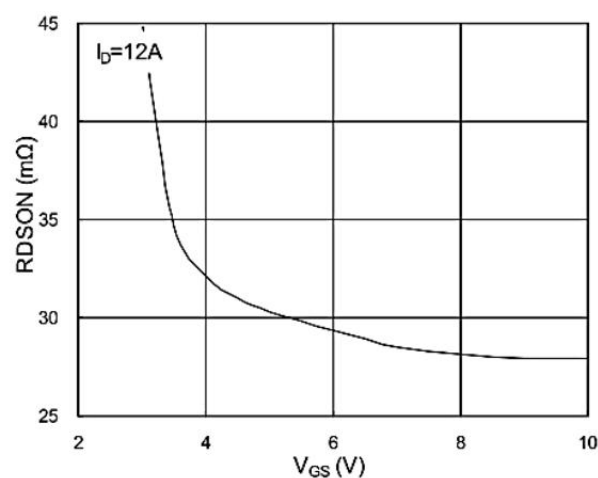


Fig.2 On-Resistance vs. Gate-Source

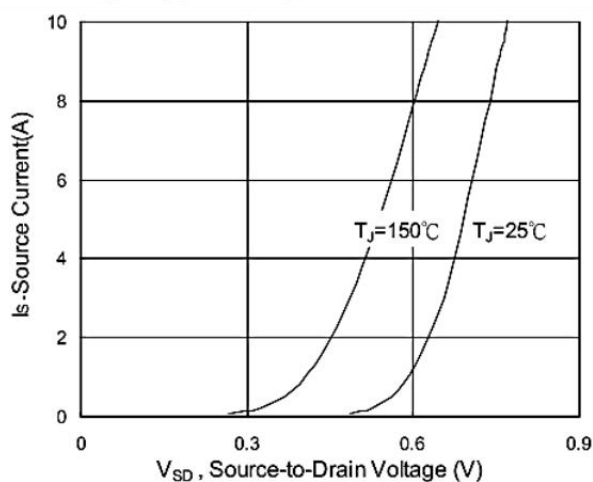


Fig.3 Forward Characteristics Of Reverse

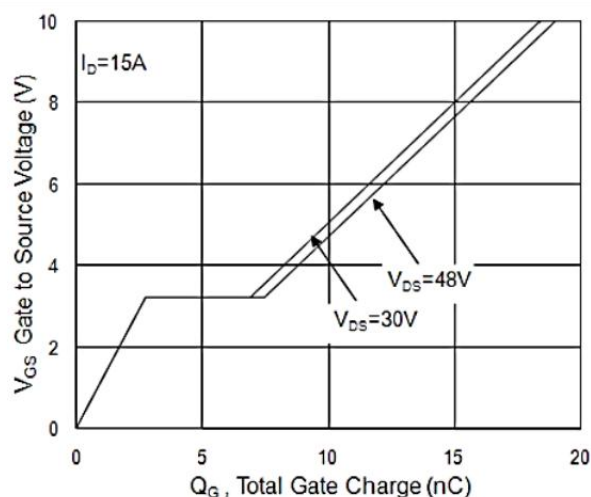


Fig.4 Gate-Charge Characteristics

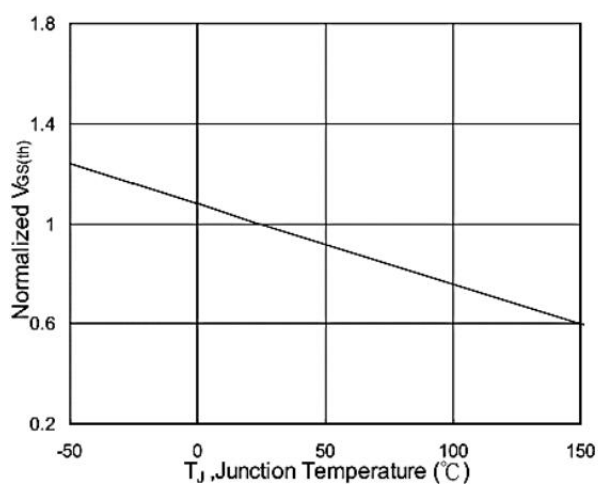


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

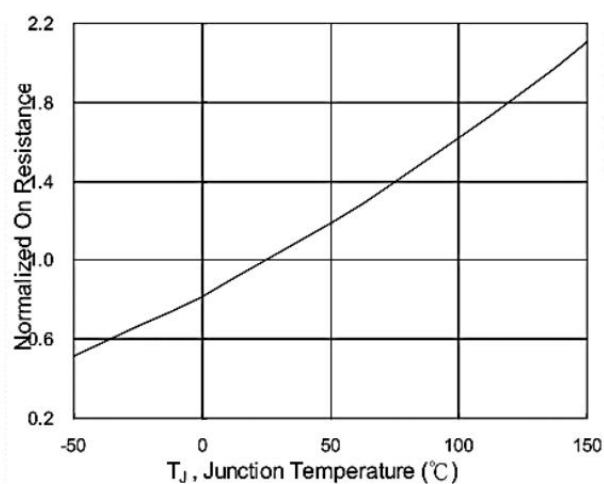


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics

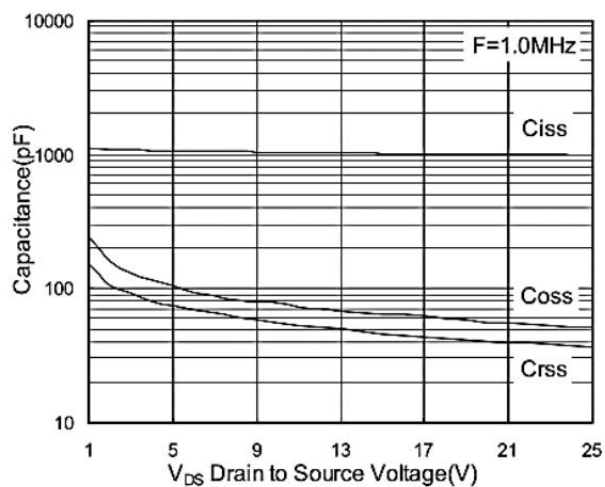


Fig.7 Capacitance

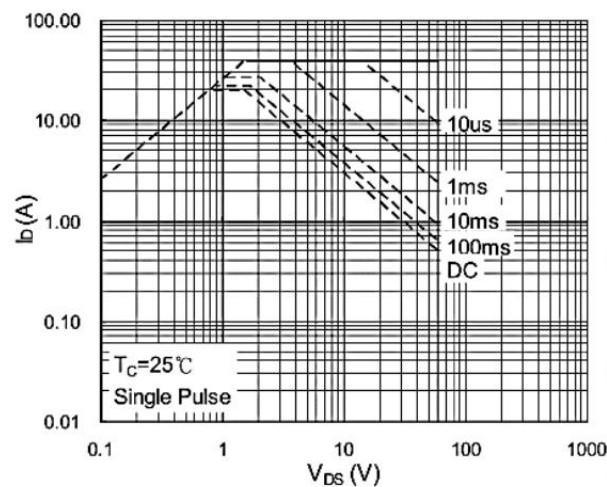


Fig.8 Safe Operating Area

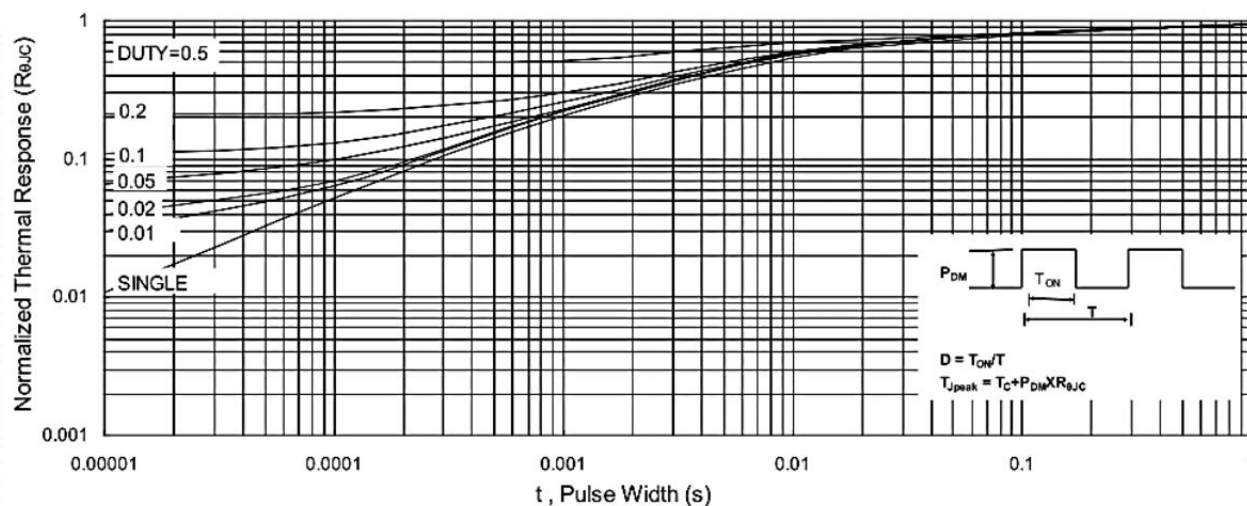


Fig.9 Normalized Maximum Transient Thermal Impedance

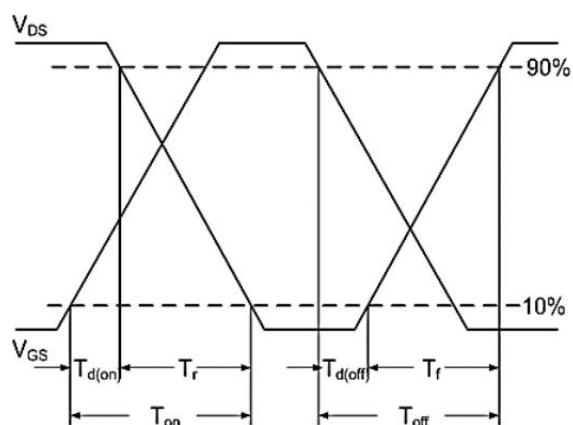


Fig.10 Switching Time Waveform

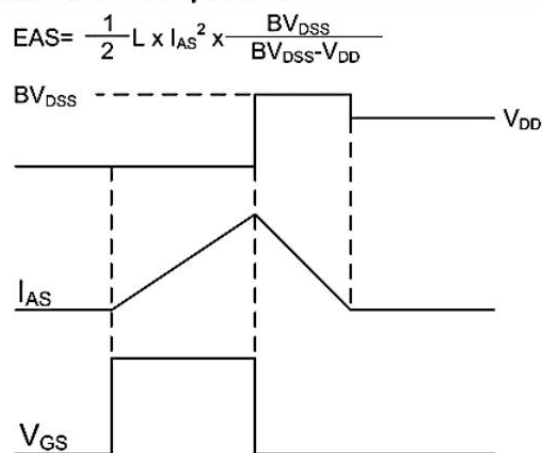
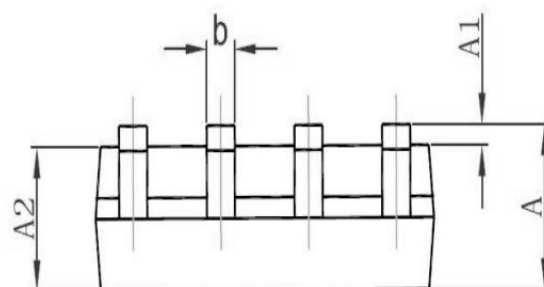
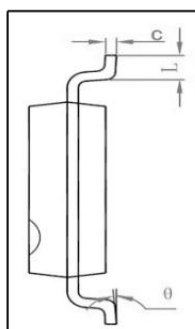
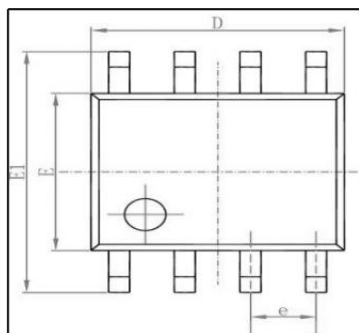
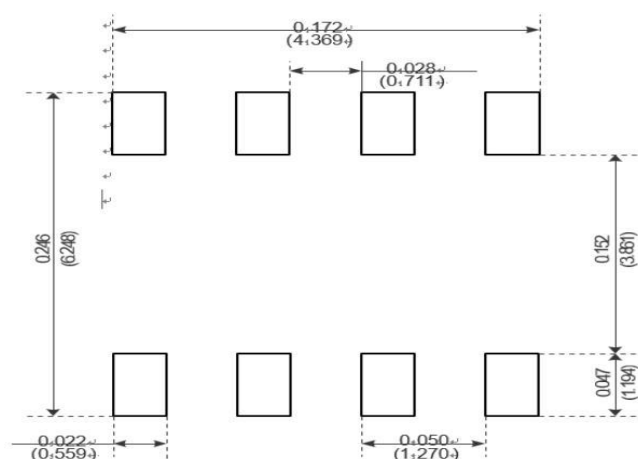


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOP-8		3000